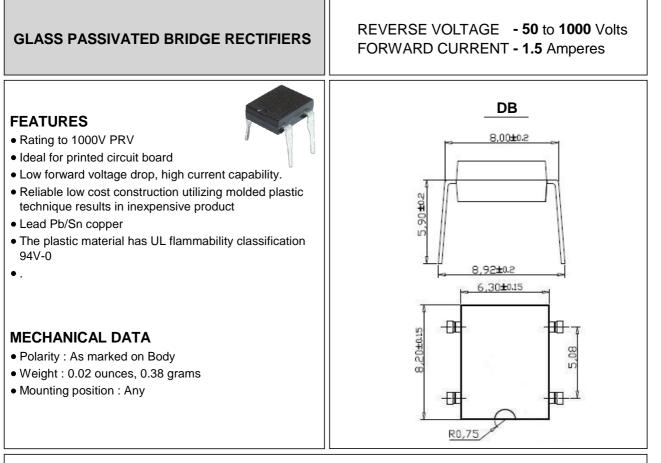
## GMGarboMicro Semiconductor

## DB150 thru DB1510



## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at  $25^{\circ}$ C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%

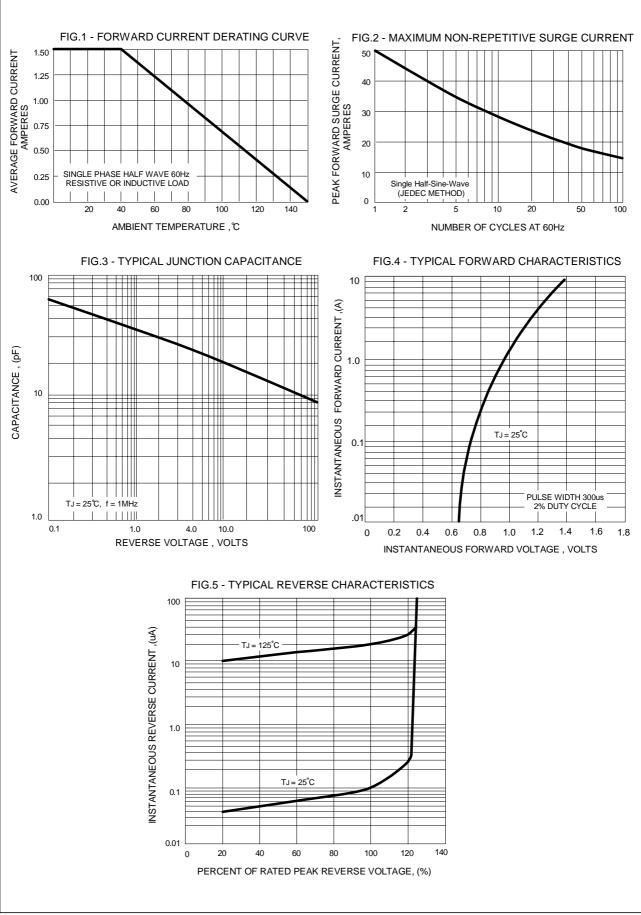
CHARACTERISTICS	SYMBOL	DB 150	DB 151	DB 152	DB 154	DB 156	DB 158	DB 1510	UNIT
Maximum Recurrent Peak Reverse Voltage	VRRM	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	VRMS	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	VDC	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current @TA=40°C	I(AV)	1.5							A
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC METHOD)	IFSM	50							A
Maximum forward Voltage at 1.5A DC	VF	1.1							V
Maximum DC Reverse Current at Rated DC Blocking Voltage@TJ =25°C @TJ =125°C	IR	10 500							uA uA
$I^2$ t Rating for fusing (t < 8.3ms)	l <sup>2</sup> t	10.4							A <sup>2</sup> S
Typical Junction Capacitance per element (Note 1)	Cı	25							pF
Typical Thermal Resistance (Note 2)	Reja	40							°C/W
Operating Temperature Range	TJ	-55 to +150							°C
Storage Temperature Range	Тѕтс	-55 to +150							°C

NOTES : 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

2.Thermal resistance from junction to ambient mounted on P.C.B with 0.5 x 0.5"(13x13mm) copper pads.

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## RATING AND CHARACTERISTIC CURVES DB150 thru DB1510



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